



# STK0260F

Advanced Power MOSFET

## SWITCHING REGULATOR APPLICATIONS

### Features

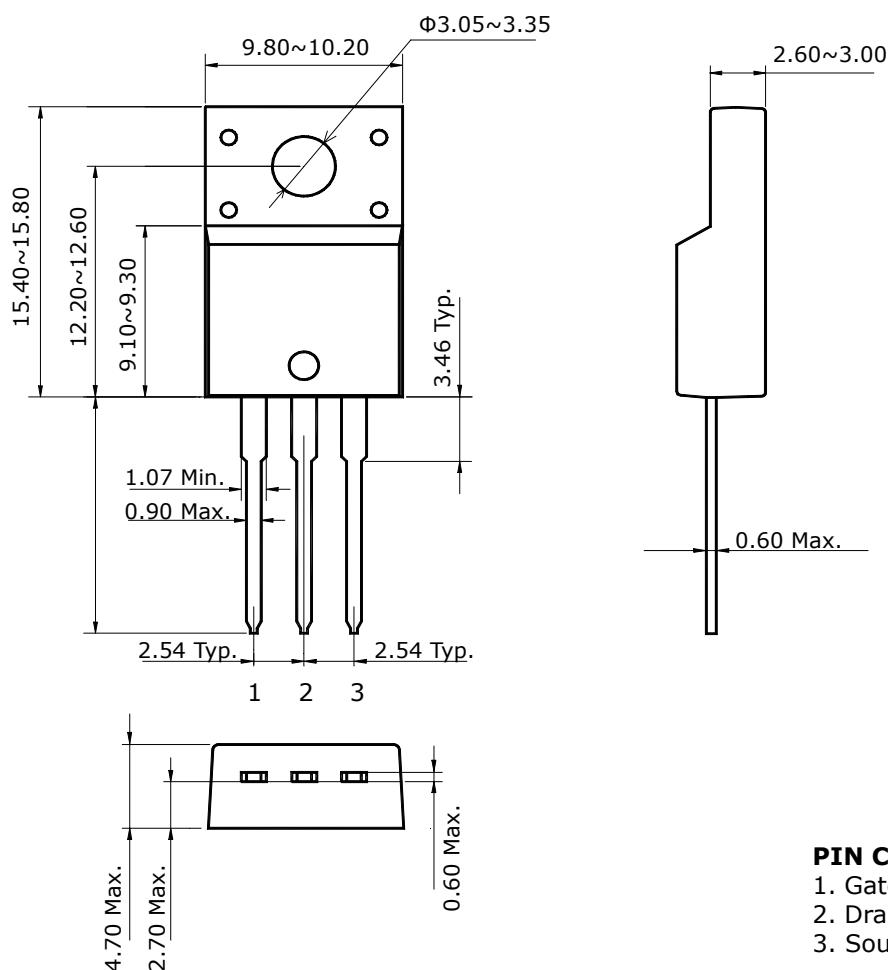
- High Voltage:  $BV_{DSS}=600V$ (Min.)
- Low  $C_{rss}$  :  $C_{rss}=6.0\text{pF}$ (Typ.)
- Low gate charge :  $Q_g=8.4\text{nC}$ (Typ.)
- Low  $R_{DS(on)}$  :  $R_{DS(on)}=4.0\Omega$ (Max.)

### Ordering Information

Type NO.	Marking	Package Code
STK0260F	STK0260	TO-220F-3L

### Outline Dimensions

unit : mm



**STK0260F****Absolute maximum ratings**

(Tc=25°C)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V <sub>DSS</sub>	600	V
Gate-source voltage	V <sub>GSS</sub>	±30	V
Drain current (DC)	I <sub>D</sub>	(Tc=25°C)	A
		(Tc=100°C)	A
Drain current (Pulsed) *	I <sub>DP</sub>	8.0	A
Drain Power dissipation	P <sub>D</sub>	22	W
Avalanche current (Single) ②	I <sub>AS</sub>	2.0	A
Single pulsed avalanche energy ②	E <sub>AS</sub>	42	mJ
Avalanche current (Repetitive) ①	I <sub>AR</sub>	2.0	A
Repetitive avalanche energy ①	E <sub>AR</sub>	3.7	mJ
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	

\* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max	Unit
Thermal resistance	R <sub>th(J-C)</sub>	-	5.68	°C/W
	R <sub>th(J-a)</sub>	-	62.5	

**STK0260F****Electrical Characteristics**

(Tc=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0	600	-	-	V
Gate-threshold voltage	V <sub>GS(th)</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> = V <sub>GS</sub>	2.0	-	4.0	V
Drain-source leakage current	I <sub>DSS</sub>	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V	-	-	±100	nA
Drain-Source on-resistance ④	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =1.0A	-	3.8	4.7	Ω
Forward transfer admittance ④	g <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1.0A	-	2.3	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	-	290	435	pF
Output capacitance	C <sub>oss</sub>		-	33	49	
Reverse transfer capacitance	C <sub>rss</sub>		-	6.0	9.0	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =300V, V <sub>GS</sub> =10V I <sub>D</sub> =2.0A, R <sub>G</sub> =25Ω ③④	-	22	-	ns
Rise time	t <sub>r</sub>		-	10.5	-	
Turn-off delay time	t <sub>d(off)</sub>		-	7	-	
Fall time	t <sub>f</sub>		-	10.5	-	
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> =300V, V <sub>GS</sub> =10V I <sub>D</sub> =2.0A ③④	-	8.4	12.6	nC
Gate-source charge	Q <sub>gs</sub>		-	1.4	2.1	
Gate-drain charge	Q <sub>gd</sub>		-	2.6	3.9	

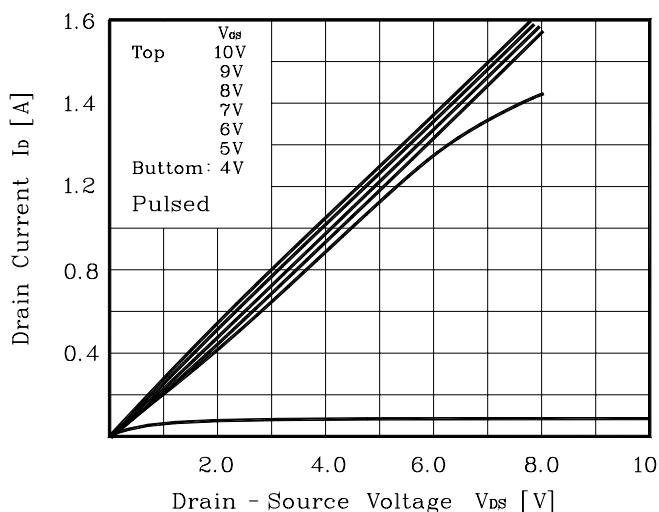
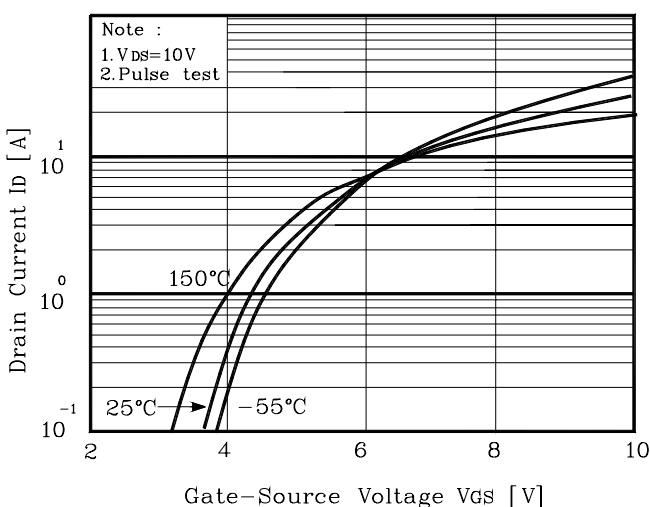
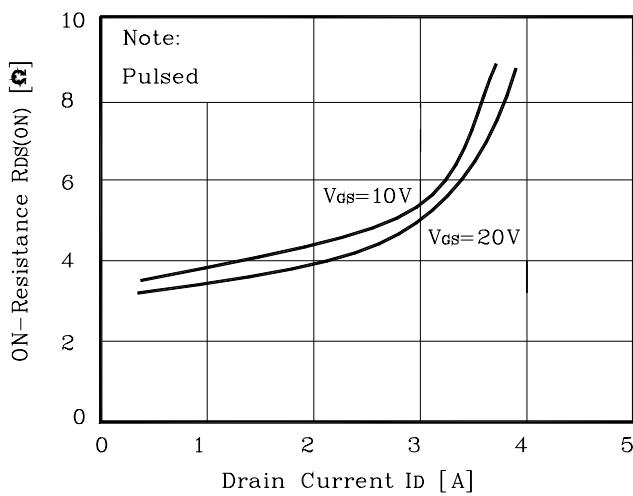
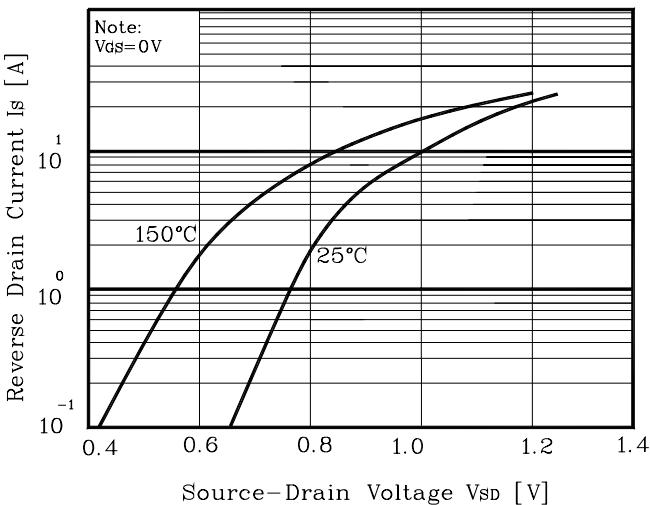
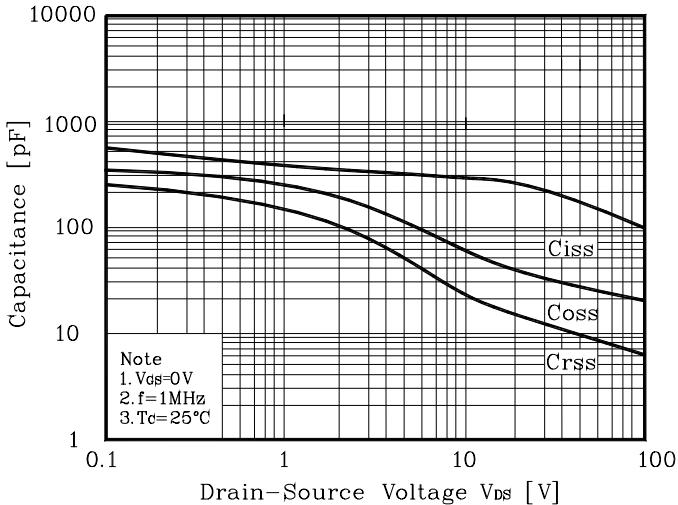
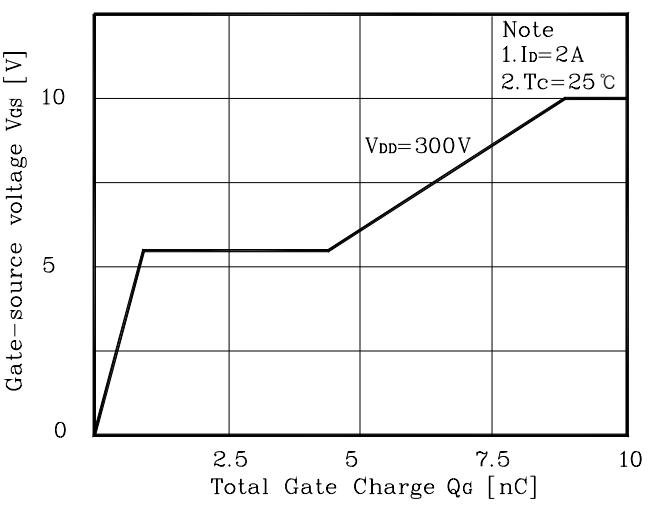
**Source-Drain Diode Ratings and Characteristics**

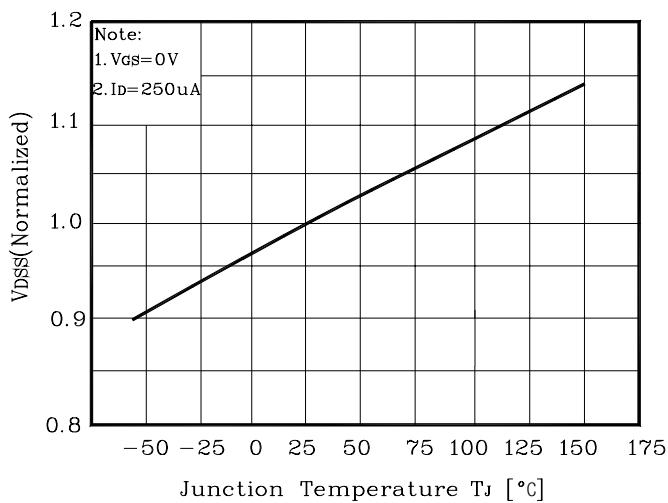
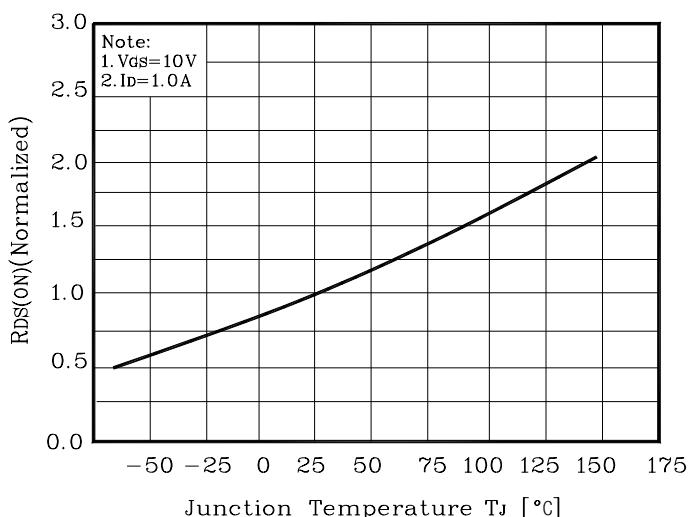
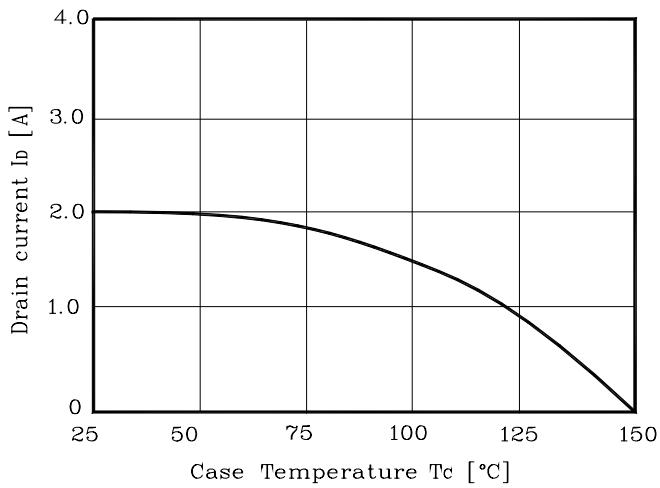
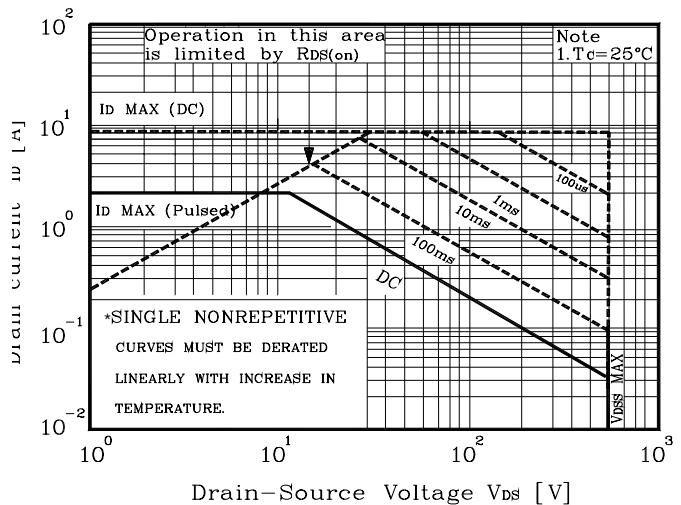
(Tc=25°C)

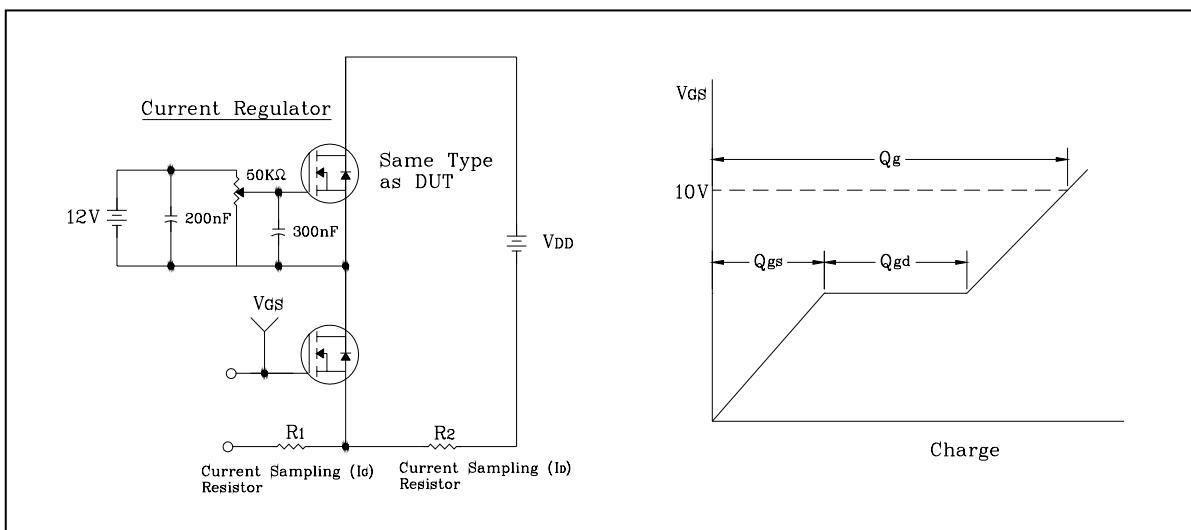
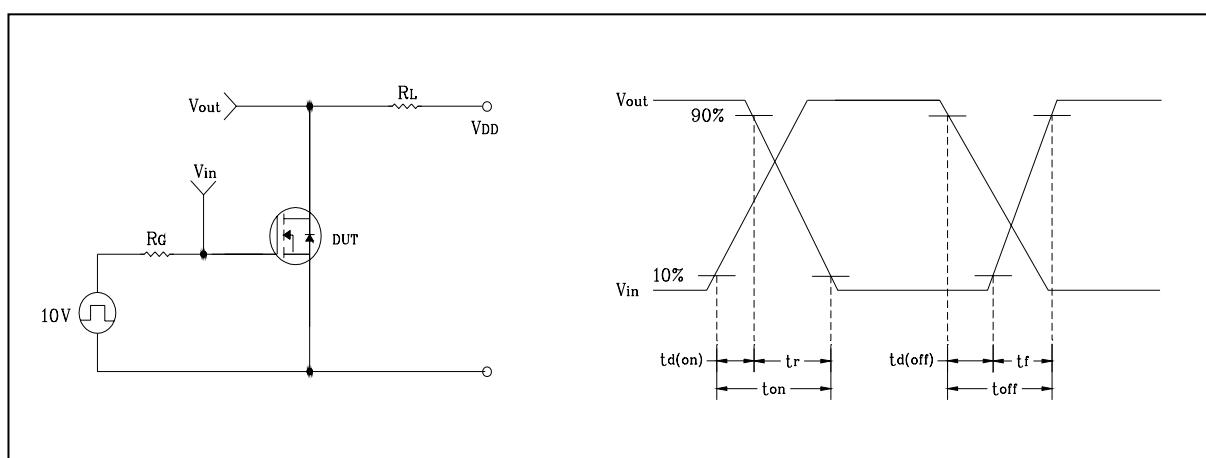
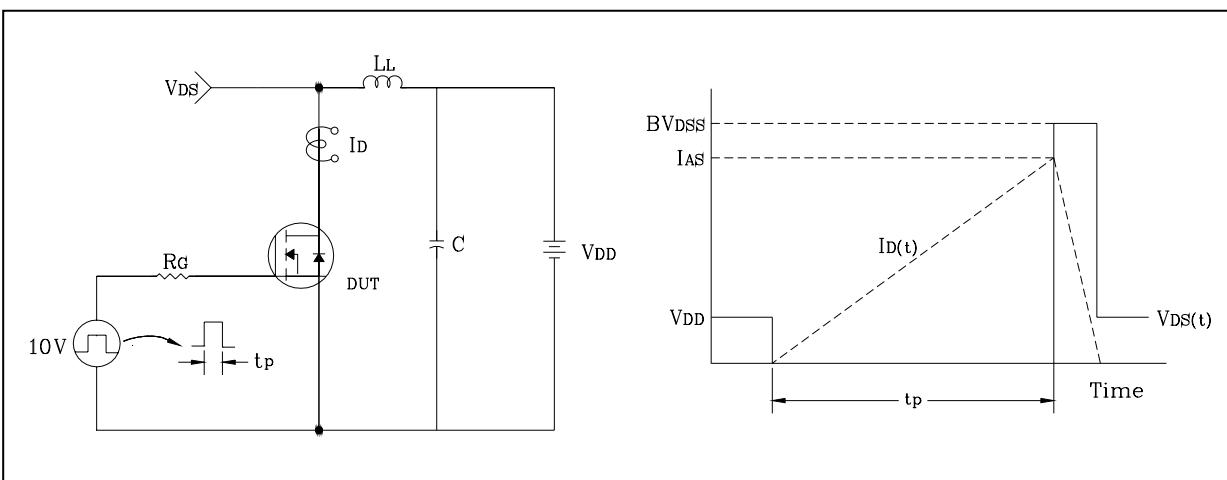
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Continuous source current	I <sub>S</sub>	Integral reverse diode in the MOSFET	-	-	2.0	A
Source current (Pulsed) ①	I <sub>SM</sub>		-	-	8.0	
Forward voltage ④	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =2.0A	-	-	1.4	V
Reverse recovery time	t <sub>rr</sub>	I <sub>s</sub> =2.0A, V <sub>GS</sub> =0V di <sub>s</sub> /dt=100A/us	-	230	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	0.84	-	uC

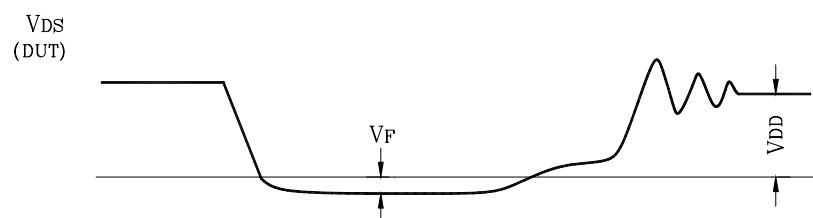
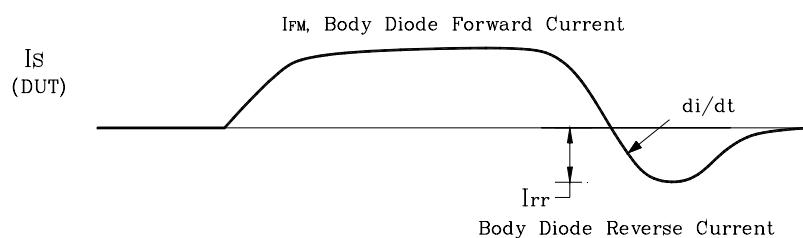
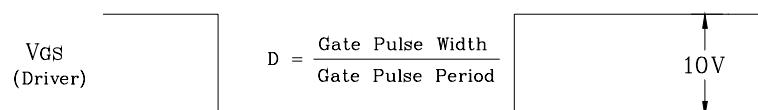
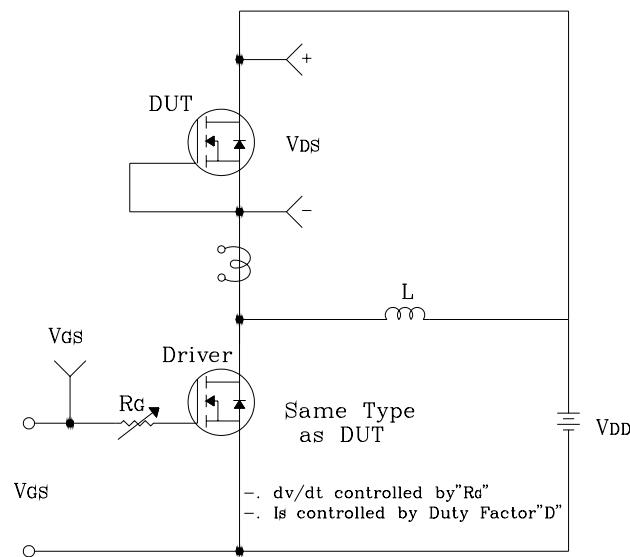
Note :

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② L=9.5mH, I<sub>AS</sub>=2.0A, V<sub>DD</sub>=50V, R<sub>G</sub>=25Ω
- ③ Pulse Test : Pulse Width < 300us, Duty cycle≤ 2%
- ④ Essentially independent of operating temperature

**Electrical Characteristic Curves****Fig. 1  $I_D$  -  $V_{DS}$** **Fig. 2  $I_D$  -  $V_{GS}$** **Fig. 3  $R_{DS(on)}$  -  $I_D$** **Fig. 4  $I_S$  -  $V_{SD}$** **Fig. 5 Capacitance -  $V_{DS}$** **Fig. 6  $V_{GS}$  -  $Q_G$** 

**STK0260F****Fig. 7 V<sub>DSS</sub> - T<sub>J</sub>****Fig. 8 R<sub>Ds(on)</sub> - T<sub>J</sub>****Fig. 9 I<sub>D</sub> - T<sub>C</sub>****Fig. 10 Safe Operating Area**

**STK0260F****Fig. 11 Gate Charge Test Circuit & Waveform****Fig. 12 Resistive Switching Test Circuit & Waveform****Fig. 13 E<sub>AS</sub> Test Circuit & Waveform**

**STK0260F****Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform**

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